# N-Channel 40-V (D-S) MOSFET

### **Key Features:**

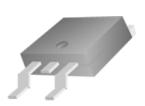
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

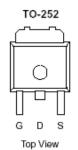
<b>Typical Applications:</b>
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)			
40	$32 @ V_{GS} = 10V$	33			
	42 @ V <sub>GS</sub> = 4.5V	29			







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage	$V_{DS}$	40	V			
Gate-Source Voltage	$V_{GS}$	±20	V			
Continuous Drain Current a	T <sub>A</sub> =25°C	$I_D$	33	Α		
Pulsed Drain Current <sup>b</sup>			50			
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	35	Α			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	50	W		
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

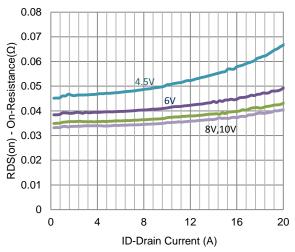
Parameter	Symbol	mbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gurrent	I <sub>DSS</sub>	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	25		u/\		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	33			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			32	mΩ	
Dialii-Source Oil-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 18 \text{ A}$			40	11122	
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		10		S	
Diode Forward Voltage	$V_{SD}$	$I_S = 17.6 \text{ A}, V_{GS} = 0 \text{ V}$		1.15		V	
Dynamic							
Total Gate Charge	$Q_g$	$V_{DS} = 20 \text{ V}, V_{GS} = 5.5 \text{ V},$		3			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 20 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 20 \text{ A}$		1.7		nC	
Gate-Drain Charge	$Q_gd$	10 - 20 A		1.0			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 20 \text{ V}, R_{L} = 1 \Omega,$		2			
Rise Time	t <sub>r</sub>	$V_{DS} = 20 \text{ V}, N_L - 1 \Omega,$ $I_D = 20 \text{ A},$		4		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		10		ns	
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN = 0 12		4			
Input Capacitance	C <sub>iss</sub>			186			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		40		pF	
Reverse Transfer Capacitance	$C_{rss}$			25			

#### **Notes**

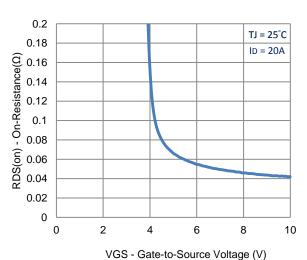
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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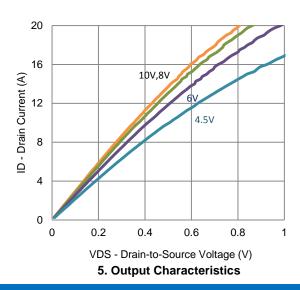
## **Typical Electrical Characteristics**

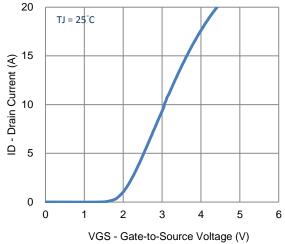


#### 1. On-Resistance vs. Drain Current

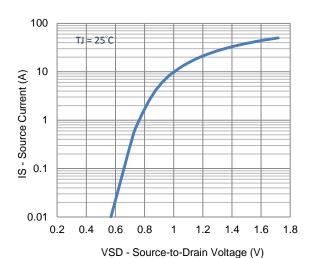


3. On-Resistance vs. Gate-to-Source Voltage

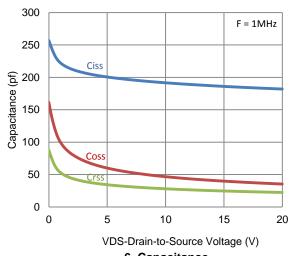




2. Transfer Characteristics

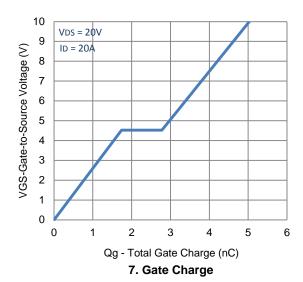


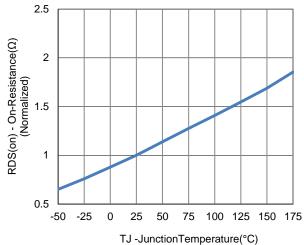
4. Drain-to-Source Forward Voltage

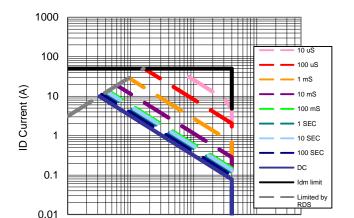


6. Capacitance

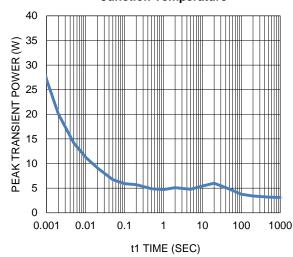
## **Typical Electrical Characteristics**







8. Normalized On-Resistance Vs
Junction Temperature



VDS Drain to Source Voltage (V)

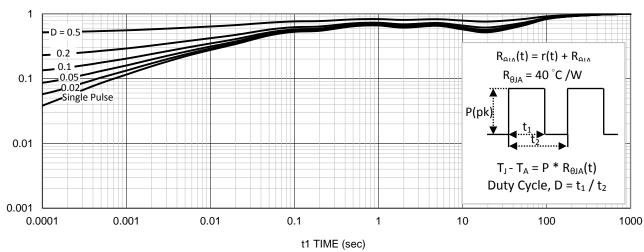
9. Safe Operating Area

10

100

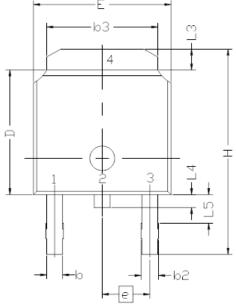
0.1

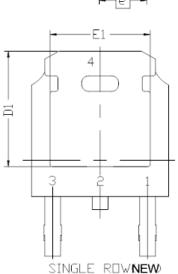
10. Single Pulse Maximum Power Dissipation

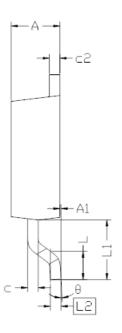


11. Normalized Thermal Transient Junction to Ambient

## **Package Information**







CVMDDI	DIMENS:	IDNAL F	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2	.743 RI	ĒF
L2	0.	.508 BS	
L3	0.89		1.27
L4 L5	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е	2.286 BSC		
e A	2,20	2,30	2.38
A1	0		0.127
_	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5,30		
E1	4.40		
θ	0°		10°

#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.